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Docket No.: M4065.0319/P319
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Ronald A. Weimer, et al.

Application No.: 09/296,835

Group Art Unit: 2813

Filed: April 22, 1999

Examiner: E. Kielin

For: FABRICATION OF DRAM AND OTHER
SEMICONDUCTOR DEVICES WITH AN
INSULATING FILM USING A WET
RAPID THERMAL OXIDATION PROCESS

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MAR 29 2002
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AMENDMENT UNDER 37 CFR 1.114

Box AF
Commissioner for Patents
Washington, DC 20231

Dear Sir:

Please amend the above-identified U.S. Patent application as follows:

In the claims:

Please add the following new claims:

SUB
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41. (new) A method of fabricating a semiconductor device comprising:

depositing a silicon nitride film over an underlying layer;

subjecting the silicon nitride film to a wet oxidation with a mixture of hydrogen and oxygen gases in a rapid thermal process chamber at a temperature of at least about 450 °C and for a duration which increases the oxygen content of the silicon nitride film; and

subjecting the silicon nitride film to a heat treatment in an ambient comprising a